TinyLogic UHS Dual Buffer with 3-STATE Outputs

Description

The NC7WZ125 is a Dual Non–Inverting Buffer with independent active LOW enables for the 3–STATE outputs. The Ultra High Speed device is fabricated with advanced CMOS technology to achieve superior switching performance with high output drive while maintaining low static power dissipation over a broad $V_{\rm CC}$ operating range. The device is specified to operate over the 1.65 V to 5.5 V $V_{\rm CC}$ operating range. The inputs and outputs are high impedance when $V_{\rm CC}$ is 0 V. Inputs tolerate voltages up to 5.5 V independent of $V_{\rm CC}$ operating range. Outputs tolerate voltages above $V_{\rm CC}$ when in the 3–STATE condition.

Features

- Space Saving US8 Surface Mount Package
- MicroPakTM Pb-Free Leadless Package
- Ultra High Speed: t_{PD} 2.6 ns Typ. into 50 pF at 5 V V_{CC}
- High Output Drive: ±24 mA at 3 V V_{CC}
- Broad V_{CC} Operating Range: 1.65 V to 5.5 V
- ullet Matches the Performance of LCX when Operated at 3.3 V V_{CC}
- Power Down High Impedance Inputs / Outputs
- Overvoltage Tolerant Inputs Facilitate 5 V to 3 V Translation
- Outputs are Overvoltage Tolerant in 3-STATE Mode
- Proprietary Noise / EMI Reduction Circuitry Implemented
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

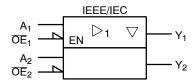


Figure 1. Logic Symbol



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MARKING DIAGRAMS



UQFN8 1.6X1.6, 0.5P CASE 523AY





US8 CASE 846AN



P3, WZ25 = Specific Device Code

KK = 2-Digit Lot Run Traceability Code XY = 2-Digit Date Code Format Z = Assembly Plant Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

Connection Diagrams

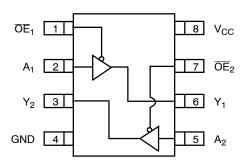


Figure 2. Connection Diagram (Top View)

ŌΕ₁ V_{CC} 8 4 GND

Figure 3. Pad Assignments for MicroPak (Top Thru View)

PIN DESCRIPTIONS

Pin Names	Description
ŌΕ _n	Enable Inputs for 3-STATE Outputs
A _n	Input
Y _n	3-STATE Outputs

FUNCTION TABLE

Inp	Output	
ŌĒ	A _n	Y _n
L	L	L
L	Н	Н
Н	L	Z
Н	Н	Z

H = HIGH Logic Level L = LOW Logic Level Z = 3-STATE

ABSOLUTE MAXIMUM RATINGS

Symbol	Para	ameter	Min	Max	Unit
V _{CC}	Supply Voltage		-0.5	6.5	V
V _{IN}	DC Input Voltage (Note 1)		-0.5	6.5	V
V _{OUT}	DC Output Voltage		-0.5	6.5	V
I _{IK}	DC Input Diode Current	V _{IN} < 0 V	-	-50	mA
I _{OK}	DC Output Diode Current	V _{OUT} < 0 V	-	-50	mA
I _{OUT}	DC Output Source / Sink Curre	ent	-	±50	mA
I _{CC} / I _{GND}	DC V _{CC} / Ground Current		-	±100	mA
T _{STG}	Storage Temperature Range		-65	+150	°C
TJ	Junction Lead Temperature un	der Bias	-	+150	°C
TL	Junction Lead Temperature (Se	oldering, 10 Seconds)	-	+260	°C
P_{D}	Power Dissipation @ +85°C		-	250	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The input and output negative voltage ratings may be exceeded if the input and output diode current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

Symbol		Parameter	Min	Max	Unit
V _{CC}	Supply Voltage Operating		1.65	5.5	V
	Supply Voltage Data Rete	ntion	1.5	5.5	
V _{IN}	Input Voltage		0	5.5	V
V _{OUT}	Output Voltage	Active State	0	V _{CC}	V
		3-STATE	0	5.5	V
T _A	Operating Temperature		-40	+85	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} @ 1.8 V ±0.15 V, 2.5 V ±0.2 V	0	20	ns/V
		V _{CC} @ 3.3 V ±0.3 V	0	10	
		V _{CC} @ 5.0 V ±0.5 V	0	5	
θ_{JA}	Thermal Resistance		-	250	°C/W

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

^{2.} Unused inputs must be held HIGH or LOW. They may not float.

DC ELECTICAL CHARACTERISTICS

					T _A = +25°C		T _A = -40	to +85°C		
Symbol	Parameter	Cond	itions	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit
V _{IH}	HIGH Level Input			1.65 to 1.95	0.65 V _{CC}	-	_	0.65 V _{CC}	=	٧
	Voltage			2.3 to 5.5	0.7 V _{CC}	-	_	0.7 V _{CC}	=	
V_{IL}	LOW Level Input			1.65 to 1.95	-	_	0.35 V _{CC}	-	0.35 V _{CC}	V
	Voltage			2.3 to 5.5	-	_	0.3 V _{CC}	-	0.3 V _{CC}	
V _{OH}	HIGH Level Output	$V_{IN} = V_{IH}$ or	$I_{OH} = -100 \mu A$	1.65	1.55	1.65	_	1.55	-	V
	Voltage	V _{IL}		2.3	2.2	2.3	_	2.2	_	
				3.0	2.9	3.0	_	2.9	_	
				4.5	4.4	4.5	_	4.4	_	
		V _{IN} = V _{IH} or	$I_{OH} = -4 \text{ mA}$	1.65	1.29	1.52	_	1.29	_	
		V _{IL}	I _{OH} = -8 mA	2.3	1.9	2.15	_	1.9	_	
			I _{OH} = -16 mA	3.0	2.4	2.80	_	2.4	_	
			I _{OH} = -24 mA	3.0	2.3	2.68	_	2.3	_	
			I _{OH} = -32 mA	4.5	3.8	4.20	_	3.8	_	
V _{OL}	LOW Level Output	$V_{IN} = V_{IH}$ or	I _{OL} = 100 μA	1.65	_	0.0	0.10	-	0.10	V
	Voltage	V _{IL}		2.3	_	0.0	0.10	-	0.10	
				3.0	_	0.0	0.10	-	0.10	
				4.5	_	0.0	0.10	-	0.10	
			I _{OL} = 4 mA	1.65	_	0.08	0.24	_	0.24	
			I _{OL} = 8 mA	2.3	-	0.10	0.3	-	0.3	
			I _{OL} = 16 mA	3.0	_	0.15	0.4	-	0.4	
			I _{OL} = 24 mA	3.0	_	0.22	0.55	-	0.55	
			I _{OL} = 32 mA	4.5	_	0.22	0.55	-	0.55	
I _{IN}	Input Leakage Current	$V_{IN} = 5.5 \text{ V, G}$	ND	1.65 to 5.5	-	-	±0.1	-	±1	μΑ
I _{OZ}	3-STATE Output Leakage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $0 \le V_{OUT} \le 5.5 \text{ V}$		1.65 to 5.5	-	-	±0.5	-	±5	μΑ
l _{OFF}	Power Off Leakage Current	V _{IN} or V _{OUT} = 5.5 V		0.0	-	-	1	-	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V, GN	ND	1.65 to 5.5	-	-	1	-	10	μΑ

NOISE CHARACTERISTICS

				T _A = +25°C		
Symbol	Parameter	Conditions	V _{CC} (V)	Тур	Max	Unit
V _{OLP} (Note 3)	Quiet Output Maximum Dynamic V _{OL}	C _L = 50 pF	5.0	-	1.0	V
V _{OLV} (Note 3)	Quiet Output Minimum Dynamic V _{OL}	C _L = 50 pF	5.0	=	1.0	V
V _{OHV} (Note 3)	Quiet Output Minimum Dynamic VOH	C _L = 50 pF	5.0	=	4.0	V
V _{IHD} (Note 3)	Minimum HIGH Level Dynamic Input Voltage	C _L = 50 pF	5.0	=	3.5	V
V _{ILD} (Note 3)	Maximum LOW Level Dynamic Input Voltage	C _L = 50 pF	5.0	=	1.5	V

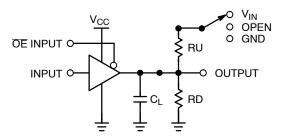
^{3.} Parameter guaranteed by design.

AC ELECTRICAL CHARACTERISTICS

					T _A = +25°C	;	T _A = -40	to +85°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay	C _L = 15 pF	1.8 ±0.15	-	-	12.0	-	13.0	ns
	A _N to Y _N (Figure 4, 6)	$R_D = 1 M\Omega$ S1 = Open	2.5 ±0.2	-	-	7.5	-	8.0	
			3.3 ±0.3	-	-	5.2	-	5.5	
			5.0 ±0.5	_	-	4.5	-	4.8	
		C _L = 50 pF,	3.3 ±0.3	-	-	5.7	-	6.0	
		$R_D = 500 \Omega$ S1 = Open	5.0 ±0.5	-	-	5.0	-	5.3	
toslh, toshl	Output to Output Skew	C _L = 50 pF,	3.3 ±0.3	_	-	1.0	-	1.0	ns
	(Note 4) (Figure 4, 6)	$R_D = 500 \Omega$ S1 = Open	5.0 ±0.5	-	-	0.8	-	0.8	
t _{PZL} , t _{PZH}		$R_{D}, R_{U} = 500 \Omega$ S1 = GND for t_{PZH}	1.8 ±0.15	_	-	14.0	-	15.0	ns
	(Figure 4, 6)		2.5 ±0.2	_	-	8.5	-	9.0	
		$S1 = V_I \text{ for } t_{PZL}$ $V_I = 2 \times V_{CC}$	3.3 ±0.3	-	-	6.2	-	6.5	
		1, = 2, 100	5.5 ±0.5	-	-	5.5	-	5.8	
t_{PLZ} , t_{PHZ}	Output Disable Time	C _L = 50 pF	1.8 ±0.15	-	-	12.0	-	13.0	ns
	(Figure 4, 6)	R_D , $R_U = 500 \Omega$ S1 = GND for t_{PZH}	2.5 ±0.2	-	-	8.0	-	8.5	
	S1 =	$S1 = V_I \text{ for } t_{PZL}$ $V_I = 2 \times V_{CC}$	3.3 ±0.3	_	-	5.7	-	6.0	
			5.0 ±0.5	_	-	4.7	-	5.0	
C _{IN}	Input Capacitance		0	_	2.5	_	-	-	pF
C _{OUT}	Output Capacitance		5.0	I	4	-	-	_	pF
C_{PD}	Power Dissipation Capacitance (Figure 5)	(Note 5)	3.3	-	10	-	-	_	pF
	Oapacitatice (Figure 5)		5.0	-	12	_	-	-	

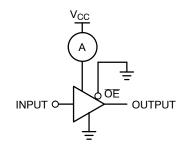
Parameter guaranteed by design. t_{OSLH} = |t_{PLHmax} - t_{PLHmin}|; t_{OSHL} = |t_{PHLmax} - t_{PHLmin}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is derived from dynamic operating current consumption (I_{CCD}) at no output loading and operating at 50% duty cycle. (see Figure 5) C_{PD} is related to I_{CCD} dynamic operating current by the expression: I_{CCD} = (C_{PD}) (V_{CC}) (f_{IN}) + (I_{CC}static).

AC Loading and Waveforms



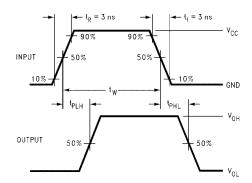
 C_L includes load and stray capacitance Input PRR = 1.0 MHz; t_W = 500 ns $\,$

Figure 4. AC Test Circuit



Input = AC Waveform; $t_r = t_f = 1.8 \text{ ns}$; PRR = 10 MHz; Duty Cycle = 50%.

Figure 5. I_{CCD} Test Circuit



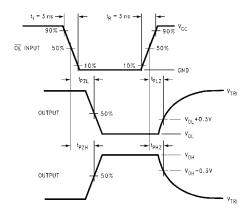


Figure 6. AC Waveforms

ORDERING INFORMATION

Order Number	Top Mark	Package	Shipping [†]
NC7WZ125K8X	WZ25	8-Lead US8, JEDEC MO-187, Variation CA 3.1 mm Wide	3000 / Tape & Reel
NC7WZ125L8X	P3	8-Lead MicroPak, 1.6 mm Wide (Pb-Free)	5000 / Tape & Reel

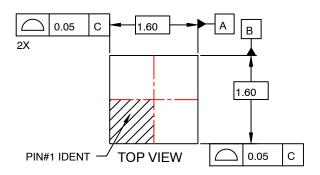
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

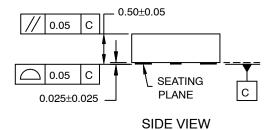
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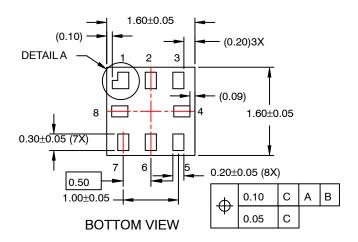
^{6.} Pb-Free package per JEDEC J-STD-020B.

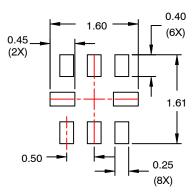
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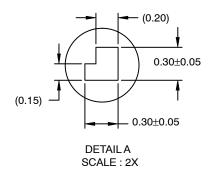




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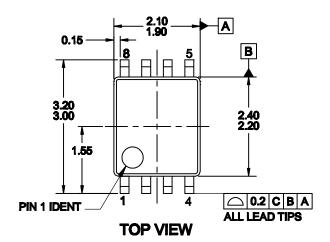


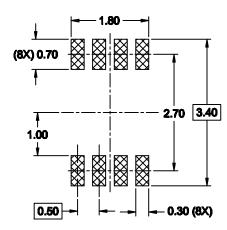
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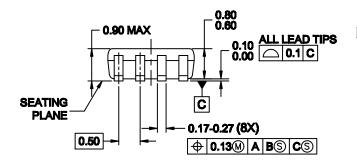
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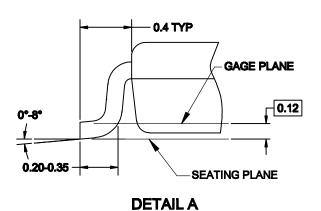
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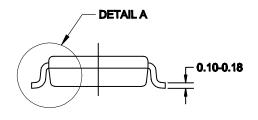


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SIDE VIEW





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